Abstracts

Low-Level Limiting Utilizing Impact Ionization in Bulk Germanium at 4.2°K

W.W. Heinz and S. Okwit. "Low-Level Limiting Utilizing Impact Ionization in Bulk Germanium at 4.2°K." 1965 G-MTT Symposium Program and Digest 65.1 (1965 [MWSYM]): 89-92.

Low-level garnet limiters operating in the coincidence region have previously been reported at 4.2°K. These devices, however, operate only within an octave frequency range, which is a function of the 4pi/M/sub s/. For YIG at 4.2°K, for example, this frequency range is 2.3 to 4.6 gc. This paper describes the application of impact ionization in bulk semiconductors to obtain low-level limiting, for which no such frequency limit exists in the microwave range.

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